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SLVS859B-JUNE 2008-REVISED DECEMBER 2014

TPS61085 650-kHz,1.2-MHz, 18.5-V Step-Up DC-DC Converter

Technical

Documents

1 Features

- 2.3 V to 6 V Input Voltage Range
- 18.5-V Boost Converter With 2.0-A Switch Current
- 650-kHz/1.2-MHz Selectable Switching Frequency
- Adjustable Soft-Start
- Thermal Shutdown
- Undervoltage Lockout
- 8-Pin VSSOP Package
- 8-Pin TSSOP Package

2 Applications

- Handheld Devices
- GPS Receivers
- Digital Still Cameras
- Portable Applications
- DSL Modems
- PCMCIA Cards
- TFT LCD Bias Supply

4 Simplified Schematic

3 Description

Tools &

Software

The TPS61085 is a high frequency, high efficiency DC-DC converter with an integrated 2.0-A, 0.13- Ω power switch capable of providing an output voltage up to 18.5 V. The selectable frequency of 650 kHz or 1.2 MHz allows the use of small external inductors and capacitors and provides fast transient response. The external compensation allows optimizing the application for specific conditions. A capacitor connected to the soft-start pin minimizes inrush current at startup.

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Device Information⁽¹⁾

| PART NUMBER | PACKAGE | BODY SIZE (NOM) |
|-------------|-----------|-------------------|
| TPS61085 | VSSOP (8) | 3.00 mm × 3.00 mm |
| | TSSOP (8) | 3.00 mm × 4.40 mm |

(1) For all available packages, see the orderable addendum at the end of the datasheet.

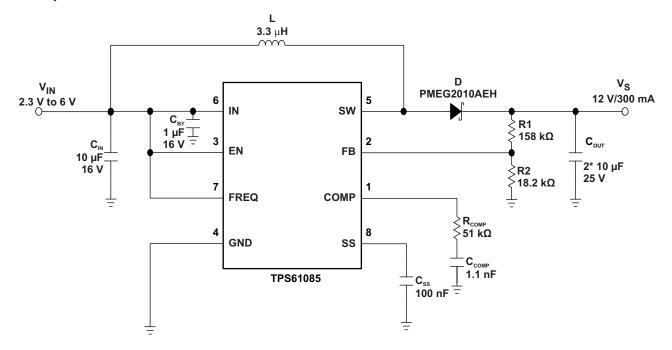


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5 Revision History

Changes from Revision A (April 2012) to Revision B

| • | Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation | |
|---|---|--|
| | section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and | |
| | Mechanical, Packaging, and Orderable Information section1 | |

Changes from Original (June 2008) to Revision A

| • | Changed the circuit illustration value of C _{COMP} From: 1.6 nF To: 1.1 nF | 1 |
|---|--|----|
| • | Deleted Lead Temperature from the Abs Max table | 3 |
| • | Added a conditions statement and two new graphs (Max Load Current vs Input Voltage) to the Typical Characteristics graphs | 5 |
| • | Added three paragraphs of text to the Detailed Description. | 7 |
| • | Changed Figure 8 to Figure 17 | 9 |
| • | Changed the Design Procudures step 3 details following Equation 4 | 10 |
| • | Changed text in the Inductor Selection section "inductor current ripple is below 20%" to " inductor current ripple is below 35%" | 10 |
| • | Changed Equation 8 | 12 |
| • | Added Used I _{OUT} to Table 5 | 12 |
| • | Added Equation 10 | 13 |
| • | Changed the White LED Applications optional Zener connection for Figure 19 to Figure 21 | 17 |

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EXAS **NSTRUMENTS**

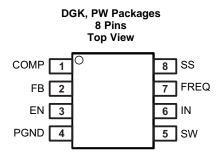
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6 Pin Configuration and Functions



8-PIN 4.9-mm × 3-mm × 1.1-mm VSSOP (DGK)

8-PIN 6.4-mm × 3-mm × 1.2-mm TSSOP (PW)

| | Pin Functions | | | |
|------|---------------|-----|---|--|
| PIN | | I/O | DESCRIPTION | |
| NAME | NO. | 1/0 | DESCRIPTION | |
| COMP | 1 | I/O | Compensation pin | |
| EN | 3 | Ι | Shutdown control input. Connect this pin to logic high level to enable the device | |
| FB | 2 | Ι | dback pin | |
| FREQ | 7 | Ι | uency select pin. The power switch operates at 650 kHz if FREQ is connected to GND and at 1.2 MHz if Q is connected to IN | |
| IN | 6 | Ι | Input supply pin | |
| PGND | 4 | | Power ground | |
| SS | 8 | 0 | Soft-start control pin. Connect a capacitor to this pin if soft-start needed. Open = no soft-start | |
| SW | 5 | Ι | Switch pin | |

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾⁽²⁾

| | MIN | MAX | UNIT |
|--|--------|-------------------|------|
| Input voltage range IN | -0.3 | 7 | V |
| Voltage range on pins EN, FB, SS, FREQ, COMP | -0.3 | 7 | V |
| Voltage on pin SW | -0.3 | 20 | V |
| Continuous power dissipation | See Th | ermal Information | |
| Operating junction temperature | -40 | 150 | °C |
| Storage temperature | -65 | 150 | °C |

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

(2) All voltage values are with respect to network ground terminal.

7.2 ESD Ratings

| | | | VALUE | UNIT |
|--------------------|-------------------------|--|-------|------|
| | | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ | ±2000 | |
| V _(ESD) | Electrostatic discharge | Charged-device model (CDM), per JEDEC specification JESD22-C101 $^{(2)}$ | ±500 | V |
| | | Machine model (MM) | ±200 | |

 JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions. Pins listed as ±XXX V may actually have higher performance.
 JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with

less than 250-V CDM is possible with the necessary precautions. Pins listed as ±YYY V may actually have higher performance.

7.3 Recommended Operating Conditions

| | | MIN | TYP MAX | UNIT |
|----------------|--------------------------------|-----------------------|---------|------|
| V_{IN} | Input voltage range | 2.3 | 6 | V |
| Vs | Boost output voltage range | V _{IN} + 0.5 | 18.5 | V |
| T _A | Operating free-air temperature | -40 | 85 | °C |
| TJ | Operating junction temperature | -40 | 125 | °C |

7.4 Thermal Information

| | | TPS | 61085 | |
|-----------------------|--|--------|--------|------|
| | THERMAL METRIC ⁽¹⁾ | DGK | PW | UNIT |
| | | 8 PINS | 8 PINS | |
| $R_{	extsf{	heta}JA}$ | Junction-to-ambient thermal resistance | 189.3 | 183.3 | |
| R _{0JC(top)} | Junction-to-case (top) thermal resistance | 57.1 | 66.7 | |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 109.9 | 112.0 | °C/W |
| Ψ_{JT} | Junction-to-top characterization parameter | 3.5 | 8.3 | |
| Ψјв | Junction-to-board characterization parameter | 108.3 | 110.3 | |

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

7.5 Electrical Characteristics

 V_{IN} = 3.3 V, EN = V_{IN} , V_S = 12 V, T_A = -40°C to 85°C, typical values are at T_A = 25°C (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|-------------------------------------|---|--------------------------|--------|-------|------|
| SUPPLY | | | | | | |
| V _{IN} | Input voltage range | | 2.3 | | 6 | V |
| l _Q | Operating quiescent current into IN | Device not switching, $V_{FB} = 1.3 V$ | | 70 | 100 | μA |
| I _{SDVIN} | Shutdown current into IN | EN = GND | | | 1 | μA |
| UVLO | Undervoltage lockout threshold | V _{IN} falling | | | 2.2 | V |
| | | V _{IN} rising | | | 2.3 | V |
| T _{SD} | Thermal shutdown | Temperature rising | | 150 | | °C |
| T _{SD(HYS)} | Thermal shutdown hysteresis | | | 14 | | °C |
| LOGIC SIG | NALS EN, FREQ | | | | | |
| V _{IH} | High level input voltage | V _{IN} = 2.3 V to 6 V | 2 | | | V |
| V _{IL} | Low level input voltage | V _{IN} = 2.3 V to 6 V | | | 0.5 | V |
| l _{ikg} | Input leakage current | EN = FREQ = GND | | | 0.1 | μA |
| BOOST CO | NVERTER | | | | | |
| Vs | Boost output voltage | | V _{IN} + 0.5 | | 18.5 | V |
| V _{FB} | Feedback regulation voltage | | 1.230 | 1.238 | 1.246 | V |
| gm | Transconductance error amplifier | | | 107 | | μA/V |
| I _{FB} | Feedback input bias current | V _{FB} = 1.238 V | | | 0.1 | μA |
| r _{DS(on)} | N-channel MOSFET on-resistance | $V_{IN} = V_{GS} = 5 V$, $I_{SW} = current limit$ | | 0.13 | 0.20 | Ω |
| | | $V_{IN} = V_{GS} = 3.3V$, $I_{SW} = current limit$ | | 0.15 | 0.24 | |
| l _{ikg} | SW leakage current | $EN = GND, V_{SW} = 6V TBD$ | | | 10 | μA |
| I _{LIM} | N-Channel MOSFET current limit | | 2.0 | 2.6 | 3.2 | А |
| I _{SS} | Soft-start current | V _{SS} = 1.238 V | 7 | 10 | 13 | μA |
| f _S | Oscillator frequency | FREQ = V _{IN} | 0.9 | 1.2 | 1.5 | MHz |
| | | FREQ = GND | 480 | 650 | 820 | kHz |
| | Line regulation | $V_{IN} = 2.3 V \text{ to } 6 V, I_{OUT} = 10 \text{ mA}$ | | 0.0002 | | %/V |
| | Load regulation | $V_{IN} = 3.3 \text{ V}, I_{OUT} = 1 \text{ mA to } 400 \text{ mA}$ | | 0.11 | | %/A |

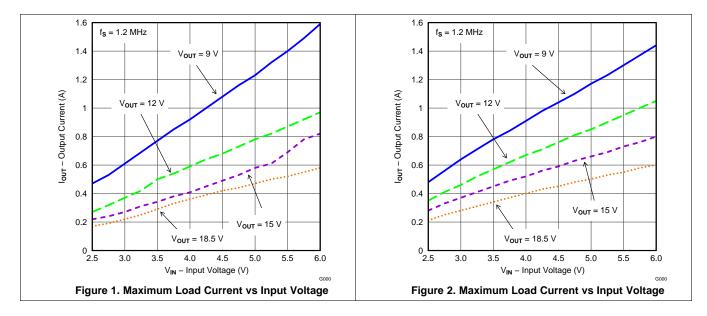


7.6 Typical Characteristics

The typical characteristics are measured with the inductors 7447789003 3.3 μ H (high frequency) or B82464G4 6.8 μ H (low frequency) from Epcos and the rectifier diode SL22.

| | | | FIGURE |
|-----------------------|----------------------|---|----------|
| I _{OUT(max)} | Maximum load ourrent | vs Input voltage at high frequency (1.2 MHz) | Figure 1 |
| | Maximum load current | vs Input voltage at low frequency (650 kHz) | Figure 2 |
| η | F #isionay | vs Load current, V_S = 12 V, V_{IN} = 3.3 V | Figure 3 |
| | Efficiency | vs Load current, $V_S = 9 V$, $V_{IN} = 3.3 V$ | Figure 4 |
| | Supply current | vs Supply voltage | Figure 5 |
| | Frequency | vs Load current | Figure 6 |
| | Frequency | vs Supply voltage | Figure 7 |

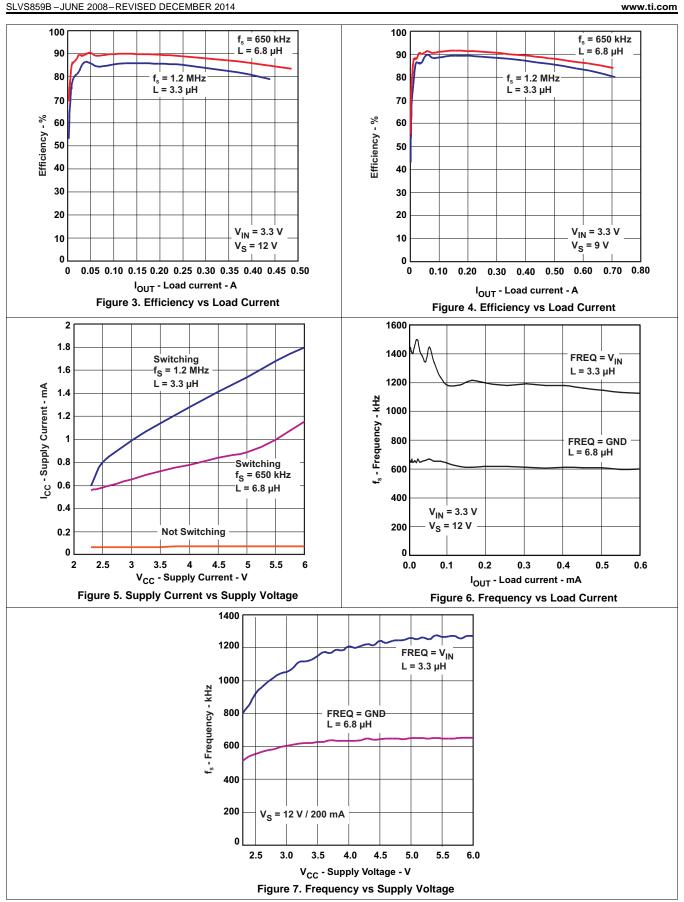




Texas INSTRUMENTS

TPS61085

SLVS859B-JUNE 2008-REVISED DECEMBER 2014



6



8 Detailed Description

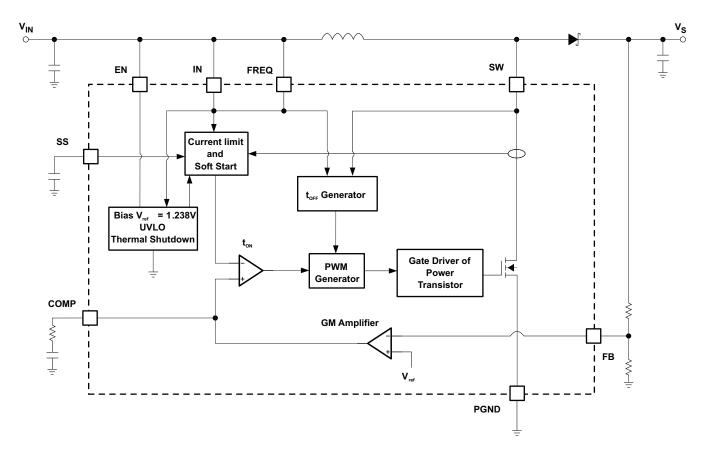
8.1 Overview

The boost converter is designed for output voltages up to 18.5 V with a switch peak current limit of 2.0 A minimum. The device, which operates in a current mode scheme with quasi-constant frequency, is externally compensated for maximum flexibility and stability. The switching frequency is selectable between 650 kHz and 1.2 MHz and the minimum input voltage is 2.3 V. To control the inrush current at start-up a soft-start pin is available.

TPS61085 boost converter's novel topology using adaptive off-time provides superior load and line transient responses and operates also over a wider range of applications than conventional converters.

The selectable switching frequency offers the possibility to optimize the design either for the use of small sized components (1.2 MHz) or for higher system efficiency (650 kHz). However, the frequency changes slightly because the voltage drop across the $r_{DS(on)}$ has some influence on the current and voltage measurement and thus on the on-time (the off-time remains constant).

The converter operates in continuous conduction mode (CCM) as soon as the input current increases above half the ripple current in the inductor, for lower load currents it switches into discontinuous conduction mode (DCM). If the load is further reduced, the part starts to skip pulses to maintain the output voltage.



8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Soft-Start

The boost converter has an adjustable soft-start to prevent high inrush current during start-up. To minimize the inrush current during start-up an external capacitor connected to the soft-start pin SS and charged with a constant current, is used to slowly ramp up the internal current limit of the boost converter when charged with a constant current. When the EN pin is pulled high, the soft-start capacitor C_{SS} is immediately charged to 0.3 V. The capacitor is then charged at a constant current of 10 µA typically until the output of the boost converter V_S has reached its Power Good threshold (roughly 98% of V_S nominal value). During this time, the SS voltage directly controls the peak inductor current, starting with 0 A at $V_{SS} = 0.3$ V up to the full current limit at $V_{SS} = 0.8$ V. The maximum load current is available after the soft-start is completed. The larger the capacitor the slower the ramp of the current limit and the longer the soft-start capacitor is discharged to ground.

8.3.2 Frequency Select Pin (FREQ)

The frequency select pin FREQ allows to set the switching frequency of the device to 650 kHz (FREQ = low) or 1.2 MHz (FREQ = high). Higher switching frequency improves load transient response but reduces slightly the efficiency. The other benefits of higher switching frequency are a lower output ripple voltage. The use of the 1.2 MHz switching frequency is recommended unless light load efficiency is a major concern.

8.3.3 Undervoltage Lockout (UVLO)

To avoid mis-operation of the device at low input voltages an undervoltage lockout is included that disables the device, if the input voltage falls below 2.2 V.

8.3.4 Thermal Shutdown

A thermal shutdown is implemented to prevent damages due to excessive heat and power dissipation. Typically the thermal shutdown threshold happens at a junction temperature of 150°C. When the thermal shutdown is triggered the device stops switching until the temperature falls below typically 136°C. Then the device starts switching again.

8.3.5 Overvoltage Prevention

If overvoltage is detected on the FB pin (typically 3 % above the nominal value of 1.238 V) the part stops switching immediately until the voltage on this pin drops to its nominal value. This prevents overvoltage on the output and secures the circuits connected to the output from excessive overvoltage.

8.4 Device Functional Modes

The converter operates in continuous conduction mode (CCM) as soon as the input current increases above half the ripple current in the inductor, for lower load currents it switches into discontinuous conduction mode (DCM). If the load is further reduced, the part starts to skip pulses to maintain the output voltage.



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPS61085 is designed for output voltages up to 18.5 V with a switch peak current limit of 2.0 A minimum. The device, which operates in a current mode scheme with quasi-constant frequency, is externally compensated for maximum flexibility and stability. The switching frequency is selectable between 650 kHz and 1.2 MHz, and the input voltage range is 2.3 V to 6.0V. To control the inrush current at start-up a soft-start pin is available. The following section provides a step-by-step design approach for configuring the TPS61085 as a voltage regulating boost converter.

9.2 Typical Application

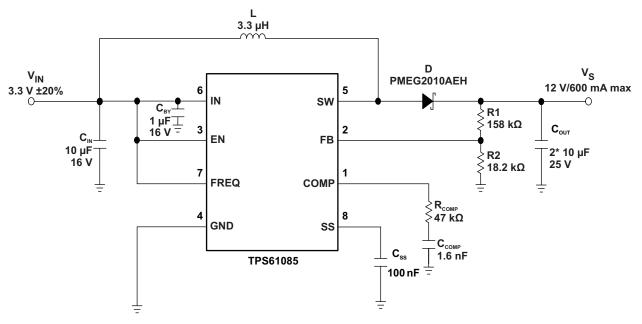


Figure 8. Typical Application, 3.3 V to 12 V ($f_s = 1.2 \text{ MHz}$)

9.2.1 Design Requirements

| Table 2 | TPS61085 | 12V | Output | Desian | Requirements |
|---------|-----------------|-----|--------|---------|---------------|
| | 11 001000 | | Output | Doorgin | noqui onionio |

| PARAMETERS | VALUES |
|---------------------|------------|
| Input Voltage | 3.3V ± 20% |
| Output Voltage | 12V |
| Output Current | 600mA |
| Switching Frequency | 1.2MHz |

9.2.2 Detailed Design Procedure

9.2.2.1 Design Procedure

The first step in the design procedure is to verify that the maximum possible output current of the boost converter supports the specific application requirements. A simple approach is to estimate the converter efficiency, by taking the efficiency numbers from the provided efficiency curves or to use a worst case assumption for the expected efficiency, e.g. 90%.

1. Duty cycle, D:

 $D = 1 - \frac{V_{IN} \cdot \eta}{V_S} \tag{1}$

2. Maximum output current, *I*_{OUT(max)}:

$$I_{OUT(\max)} = \left(I_{LIM(\min)} - \frac{\Delta I_L}{2}\right) \cdot (1 - D)$$
(2)

3. Peak switch current in application, $I_{SW(peak)}$:

$$I_{SW(peak)} = \frac{\Delta I_L}{2} + \frac{I_{OUT}}{1 - D}$$
(3)

with the inductor peak-to-peak ripple current, ΔI_L

$$\Delta I_L = \frac{V_{IN} \cdot D}{f_S \cdot L} \tag{4}$$

and

| V _{IN} | Minimum input voltage |
|-----------------------|--|
| Vs | Output voltage |
| I _{LIM(min)} | Converter switch current limit (minimum switch current limit = 3.2 A) |
| f _S | Converter switching frequency (typically 1.2 MHz or 650 kHz) |
| L | Selected inductor value |
| η | Estimated converter efficiency (please use the number from the efficiency plots or 90% as an estimation) |
| | |

The peak switch current is the steady state peak switch current that the integrated switch, inductor and external Schottky diode has to be able to handle. The calculation must be done for the minimum input voltage where the peak switch current is the highest.

9.2.2.2 Inductor Selection

The TPS61085 is designed to work with a wide range of inductors. The main parameter for the inductor selection is the saturation current of the inductor which should be higher than the peak switch current as calculated in the *Design Procedure* section with additional margin to cover for heavy load transients. An alternative, more conservative, is to choose an inductor with a saturation current at least as high as the maximum switch current limit of 3.2 A. The other important parameter is the inductor DC resistance. Usually, the lower the DC resistance the higher the efficiency. It is important to note that the inductor DC resistance is not the only parameter determining the efficiency. Especially for a boost converter where the inductor is the energy storage element, the type and core material of the inductor influences the efficiency as well. At high switching frequencies of 1.2 MHz inductor core losses, proximity effects and skin effects become more important. Usually, an inductor with a larger form factor gives higher efficiency. The efficiency difference between different inductors can vary between 2% to 10%. For the TPS61085, inductor values between 3 μ H and 6 μ H are a good choice with a switching frequency of 1.2 MHz, typically 3.3 μ H. At 650 kHz inductors between 6 μ H and 13 μ H, typically 6.8 μ H are recommended. Possible inductors are shown in Table 3.

Typically, it is recommended that the inductor current ripple is below 35% of the average inductor current. Therefore, the following equation can be used to calculate the inductor value, *L*:

$$L = \left(\frac{V_{IN}}{V_s}\right)^2 \cdot \left(\frac{V_s - V_{IN}}{I_{OUT} \cdot f_s}\right) \cdot \left(\frac{\eta}{0.35}\right)$$

with

V_{IN} Minimum input voltage

V_S Output voltage

*I*_{out} Maximum output current in the application

*f*_S Converter switching frequency (typically 1.2 MHz or 650 kHz)

 η Estimated converter efficiency (please use the number from the efficiency plots or 90% as an estimation)

| L (µH) | SUPPLIER COMPONENT | | SIZE (L×W×H mm) | DCR TYP (mΩ) | Isat (A) | | | | | |
|-----------|--------------------|-------------|--------------------|-----------------|----------|--|--|--|--|--|
| | 1.2 MHz | | | | | | | | | |
| 3.3 | Sumida | CDH38D09 | 4 x 4 x 1 | 240 | 1.25 | | | | | |
| 4.7 | Sumida | CDPH36D13 | 5 × 5 × 1.5 | 155 | 1.36 | | | | | |
| 3.3 | Sumida | CDPH4D19F | 5.2 x 5.2 x 2 | 33 | 1.5 | | | | | |
| 3.3 | Sumida | CDRH6D12 | 6.7 x 6.7 x 1.5 | 62 | 2.2 | | | | | |
| 4.7 | Würth Elektronik | 7447785004 | 5.9 × 6.2 × 3.3 | 60 | 2.5 | | | | | |
| 5 | Coilcraft | MSS7341 | 7.3 × 7.3 × 4.1 | 24 | 2.9 | | | | | |
| | • | 650 kHz | • | | | | | | | |
| 6.8 | Sumida | CDP14D19 | 5.2 x 5.2 x 2 | 50 | 1 | | | | | |
| 10 | Coilcraft | LPS4414 | 4.3 × 4.3 × 1.4 | 380 | 1.2 | | | | | |
| 6.8 | Sumida | CDRH6D12/LD | 6.7 x 6.7 x 1.5 | 95 | 1.25 | | | | | |
| 10 | Sumida | CDR6D23 | 5 × 5 × 2.4 | 133 | 1.75 | | | | | |
| 10 | Würth Elektronik | 744778910 | 7.3 × 7.3 × 3.2 | 51 | 2.2 | | | | | |
| 6.8 | Sumida | CDRH6D26HP | 7 x 7 x 2.8 | 52 | 2.9 | | | | | |

Table 3. Inductor Selection

9.2.2.3 Rectifier Diode Selection

To achieve high efficiency, a Schottky type should be used for the rectifier diode. The reverse voltage rating should be higher than the maximum output voltage of the converter. The averaged rectified forward current I_{avg} , the Schottky diode needs to be rated for, is equal to the output current I_{OUT} :

$$I_{avg} = I_{OUT}$$

Usually a Schottky diode with 2 A maximum average rectified forward current rating is sufficient for most applications. The Schottky rectifier can be selected with lower forward current capability depending on the output current I_{out} but has to be able to dissipate the power. The dissipated power, P_D , is the average rectified forward current times the diode forward voltage, $V_{forward}$.

$$P_D = I_{avg} \cdot V_{forward}$$

(7)

(6)

Typically the diode should be able to dissipate around 500mW depending on the load current and forward voltage.

| CURRENT RATING lavg | Vr | V _{forward} / lavg | SUPPLIER | COMPONENT CODE | PACKAGE TYPE | | | | |
|------------------------|------|-----------------------------|-------------------------|-------------------|-----------------|--|--|--|--|
| 750 mA | 20 V | 0.425 V / 750 mA | Fairchild Semiconductor | FYV0704S | SOT 23 | | | | |
| 1 A | 20 V | 0.39 V / 1 A | NXP | PMEG2010AEH | SOD 123 | | | | |
| 1 A | 20 V | 0.52 V / 1 A | Vishay Semiconductor | B120 | SMA | | | | |
| 1 A | 20 V | 0.5 V / 1 A | Vishay Semiconductor | SS12 | SMA | | | | |

Table 4. Rectifier Diode Selection

STRUMENTS

| CURRENT RATING lavg | Vr | V _{forward} / lavg | SUPPLIER | COMPONENT CODE | PACKAGE TYPE | | | | | |
|------------------------|------|-----------------------------|----------------------|-------------------|------------------------|--|--|--|--|--|
| 1 A | 20 V | 0.44 V / 1 A | Vishay Semiconductor | MSS1P2L | µ-SMP (Low Profile) | | | | | |

Table 4. Rectifier Diode Selection (continued)

9.2.2.4 Setting the Output Voltage

The output voltage is set by an external resistor divider. Typically, a minimum current of 50 μ A flowing through the feedback divider gives good accuracy and noise covering. A standard low side resistor of 18 k Ω is typically selected. The resistors are then calculated as:

9.2.2.5 Compensation (COMP)

The regulator loop can be compensated by adjusting the external components connected to the COMP pin. The COMP pin is the output of the internal transconductance error amplifier.

Standard values of $R_{COMP} = 13 k\Omega$ and $C_{COMP} = 3.3 nF$ will work for the majority of the applications.

See Table 5 for dedicated compensation networks giving an improved load transient response. The following equations can be used to calculate R_{COMP} and C_{COMP} :

$$R_{COMP} = \frac{110 \cdot V_{IN} \cdot V_S \cdot C_{OUT}}{L \cdot I_{OUT}} \qquad C_{COMP} = \frac{V_s \cdot C_{OUT}}{7.5 \cdot I_{OUT} \cdot R_{COMP}}$$
(9)

with

| V _{IN} | Minimum input voltage |
|------------------|---|
| Vs | Output voltage |
| Cout | Output capacitance |
| L | Inductor value, e.g. 3.3 µH or 6.8 µH |
| I _{OUT} | Maximum output current in the application |
| | |

Make sure that $R_{COMP} < 120 \ k\Omega$ and $C_{COMP} > 820 \ pF$, independent of the results of the above formulas.

Table 5. Recommended Compensation Network Values at High/Low Frequency

| Table 6. Recommended compensation network values at high/Low requeitoy | | | | | | | | | |
|--|--------|----------------|-----------------------|-------------------|-------------------|-----------------------|--|--|--|
| FREQUENCY | L | ٧ _s | V _{IN} ± 20% | R _{COMP} | C _{COMP} | Used I _{OUT} | | | |
| | | 15 V | 5 V | 82 kΩ | 1.1 nF | 0.7A | | | |
| | | 15 V | 3.3 V | 75 kΩ | 1.6 nF | 0.5A | | | |
| | 0.0 | 40.1/ | 5 V | 51 kΩ | 1.1 nF | 0.9A | | | |
| High (1.2 MHz) | 3.3 µH | 12 V | 3.3 V | 47 kΩ | 1.6 nF | 0.6A | | | |
| | | | 5 V | 30 kΩ | 1.1 nF | 1.2A | | | |
| | | 9 V | 3.3 V | 27 kΩ | 1.6 nF | 0.8A | | | |
| | | | 5 V | 43 kΩ | 2.2 nF | 0.7A | | | |
| | | 15 V | 3.3 V | 39 kΩ | 3.3 nF | 0.5A | | | |
| L (050 L L | 0.0 | 40.14 | 5 V | 27 kΩ | 2.2 nF | 0.9A | | | |
| Low (650 kHz) | 6.8 µH | 12 V | 3.3 V | 24 kΩ | 3.3 nF | 0.6A | | | |
| | | 0.1/ | 5 V | 15 kΩ | 2.2 nF | 1.2A | | | |
| | | 9 V | 3.3 V | 13 kΩ | 3.3 nF | 0.8A | | | |



Table 5 gives conservative R_{COMP} and C_{COMP} values for certain inductors, input and output voltages providing a very stable system. For a faster response time, a higher R_{COMP} value can be used to enlarge the bandwidth, as well as a slightly lower value of C_{COMP} to keep enough phase margin. These adjustments should be performed in parallel with the load transient response monitoring of TPS61087.

9.2.2.6 Input Capacitor Selection

For good input voltage filtering low ESR ceramic capacitors are recommended. TPS61085 has an analog input IN. Therefore, a 1 μ F bypass is highly recommended as close as possible to the IC from IN to GND.

One 10 µF ceramic input capacitors are sufficient for most of the applications. For better input voltage filtering this value can be increased. Refer to Table 6 and typical applications for input capacitor recommendations.

9.2.2.7 Output Capacitor Selection

For best output voltage filtering a low ESR output capacitor like ceramic capcaitor is recommended. Two 10 μ F ceramic output capacitors (or one 22 μ F) work for most of the applications. Higher capacitor values can be used to improve the load transient response. Refer to Table 6 for the selection of the output capacitor.

Table 6. Rectifier Input and Output Capacitor Selection

| | CAPACITOR | VOLTAGE RATING | SUPPLIER | COMPONENT CODE |
|------------------|------------|----------------|-------------|-----------------|
| C _{IN} | 10 µF/1206 | 16 V | Taiyo Yuden | EMK212 BJ 106KG |
| IN bypass | 1 µF/0603 | 16 V | Taiyo Yuden | EMK107 BJ 105KA |
| C _{OUT} | 10 µF/1206 | 25 V | Taiyo Yuden | TMK316 BJ 106KL |

To calculate the output voltage ripple, Equation 10 can be used:

$$\Delta V_C = \frac{V_S - V_{IN}}{V_S \cdot f_S} \cdot \frac{I_{OUT}}{C_{OUT}} \qquad \qquad \Delta V_{C_ESR} = I_{L(peak)} \cdot R_{C_ESR}$$
(10)

with

| ΔV_C | Output voltage ripple dependent on output capacitance,output current and switching frequency |
|----------------------|--|
| Vs | Output voltage |
| V _{IN} | Minimum input voltage of boost converter |
| f _S | Converter switching frequency (typically 1.2 MHz or 650 kHz) |
| lout | Output capacitance |
| $\Delta V_{C_{ESR}}$ | Output voltage ripple due to output capacitors ESR (equivalent series resistance) |
| I _{SWPEAK} | Inductor peak switch current in the application |
| R_{C_ESR} | Output capacitors equivalent series resistance (ESR) |
| A) / | na ha nada tadin manu ana sina ananis ana sitan ana ida law FCR |

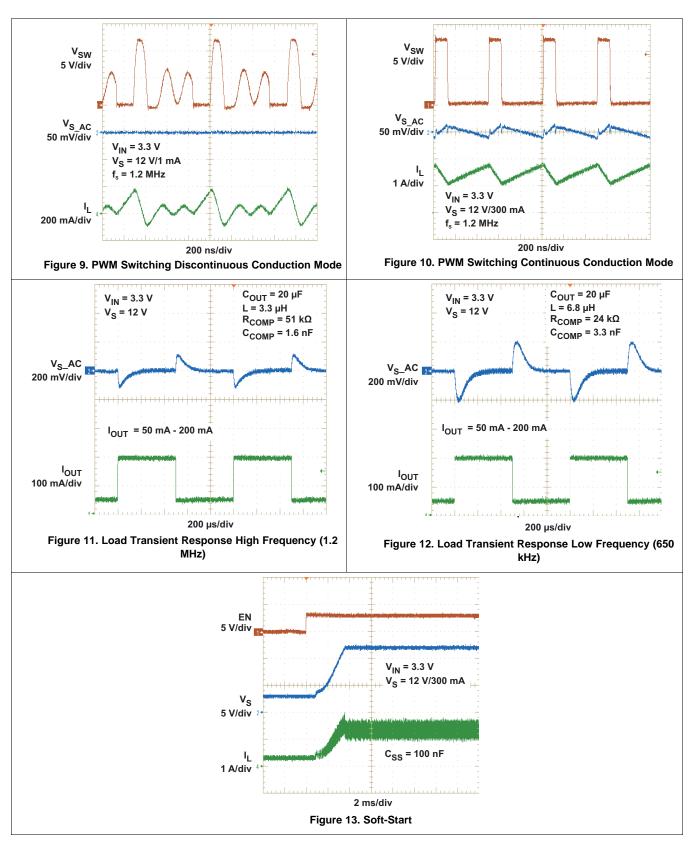
 $\Delta V_{C_{ESR}}$ can be neglected in many cases since ceramic capacitors provide low ESR.

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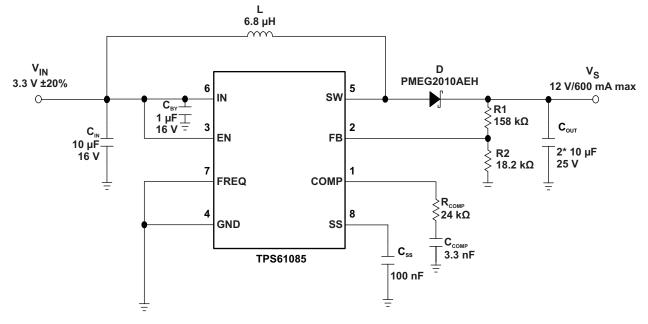
9.2.3 Application Curves



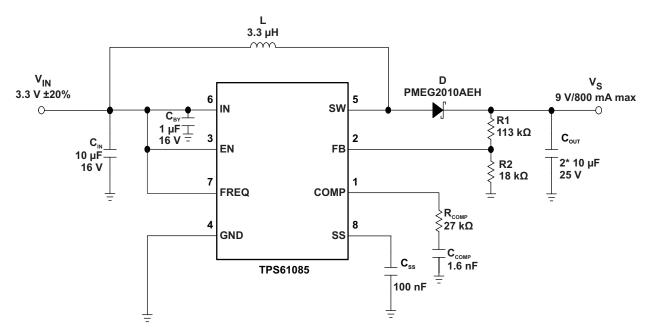


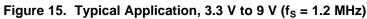
9.3 System Examples



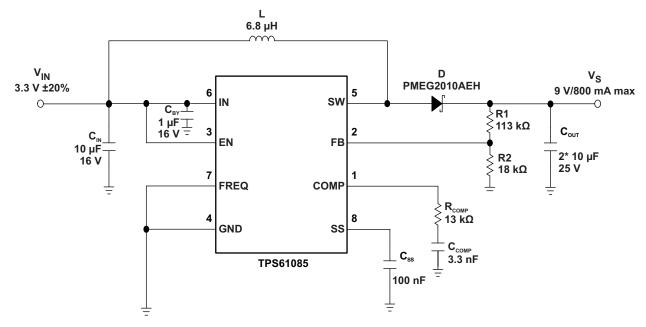








System Examples (continued)





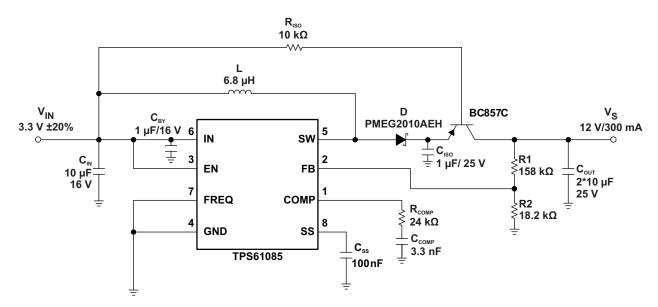


Figure 17. Typical Application With External Load Disconnect Switch



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System Examples (continued)

9.3.2 TFT LCD Application Circuit

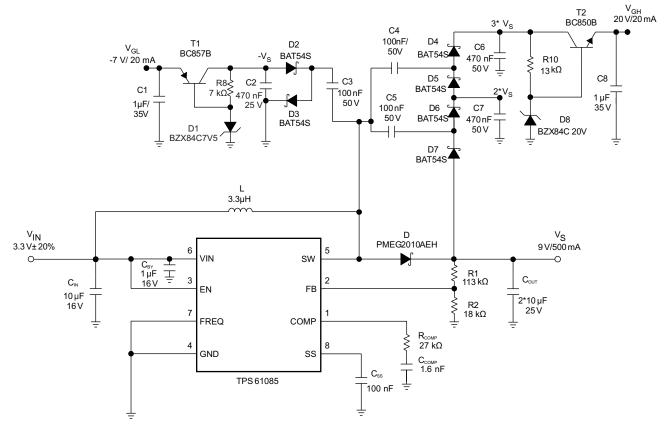
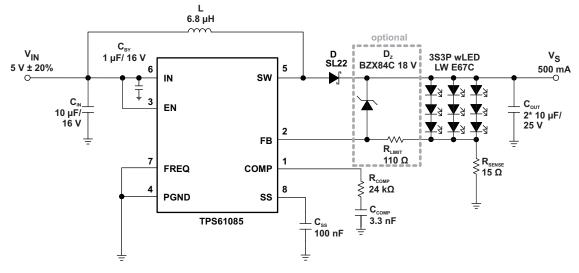


Figure 18. Typical Application 3.3 V to 9 V (f_S = 1.2 MHz) for TFT LCD With External Charge Pumps (VGH, VGL)

9.3.3 WHITE LED Application Circuits





System Examples (continued)

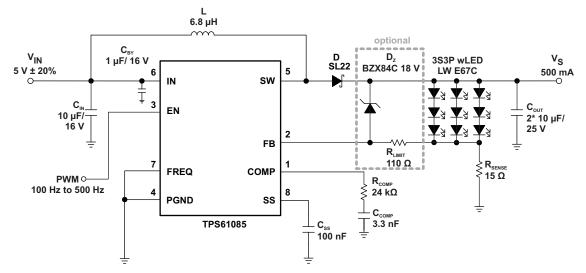


Figure 20. Simple Application (3.3V Input - f_{sw} = 650 kHz) for wLED Supply (3S3P) With Adjustable Brightness Control Using a PWM Signal on the Enable Pin (With Optional Clamping Zener Diode)

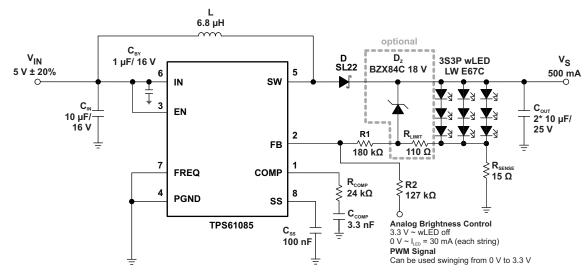


Figure 21. Simple Application (3.3 V Input - f_{sw} = 650 kHz) for wLED Supply (3S3P) With Adjustable Brightness Control Using an Analog Signal on the Feedback Pin (With Optional Clamping Zener Diode)

10 Power Supply Recommendations

The TPS61085 is designed to operate from an input voltage supply range between 2.3 V and 6.0 V. The power supply to the TPS61085 needs to have a current rating according to the supply voltage, output voltage and output current of the TPS61085.



11 Layout

11.1 Layout Guidelines

For all switching power supplies, the layout is an important step in the design, especially at high peak currents and high switching frequencies. If the layout is not carefully done, the regulator could show stability problems as well as EMI problems. Therefore, use wide and short traces for the main current path and for the power ground tracks. The input capacitor, output capacitor, and the inductor should be placed as close as possible to the IC. Use a common ground node for power ground and a different one for control ground to minimize the effects of ground noise. Connect these ground nodes at the GND terminal of the IC. The most critical current path for all boost converters is from the switching FET, through the rectifier diode, then the output capacitors, and back to ground of the switching FET. Therefore, the output capacitors and their traces should be placed on the same board layer as the IC and as close as possible between the IC's SW and GND terminal.

11.2 Layout Example

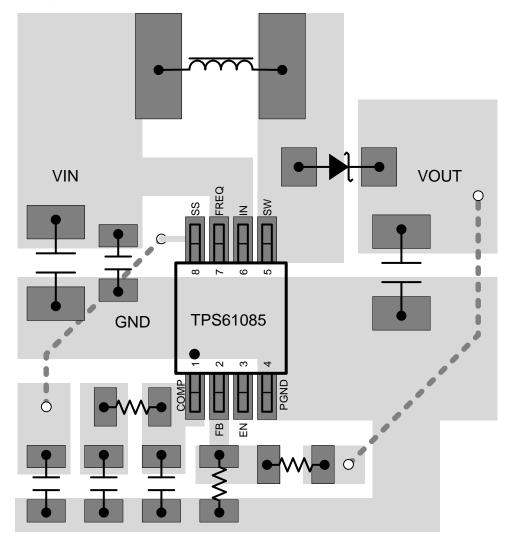
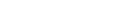


Figure 22. TPS61085 Layout Example



12 Device and Documentation Support

12.1 Trademarks

All trademarks are the property of their respective owners.

12.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

STRUMENTS

EXAS



15-Apr-2017

PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish (6) | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|----------------------------|-------------------------|--------------------|--------------|-------------------------|---------|
| HPA01142PWR | ACTIVE | TSSOP | PW | 8 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 61085 | Samples |
| TPS61085DGKR | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | РМКІ | Samples |
| TPS61085DGKRG4 | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | РМКІ | Samples |
| TPS61085DGKT | ACTIVE | VSSOP | DGK | 8 | 250 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | РМКІ | Samples |
| TPS61085DGKTG4 | ACTIVE | VSSOP | DGK | 8 | 250 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | РМКІ | Samples |
| TPS61085PW | ACTIVE | TSSOP | PW | 8 | 150 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 61085 | Samples |
| TPS61085PWG4 | ACTIVE | TSSOP | PW | 8 | 150 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 61085 | Samples |
| TPS61085PWR | ACTIVE | TSSOP | PW | 8 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 61085 | Samples |
| TPS61085PWRG4 | ACTIVE | TSSOP | PW | 8 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 61085 | Samples |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)



15-Apr-2017

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPS61085 :

• Automotive: TPS61085-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



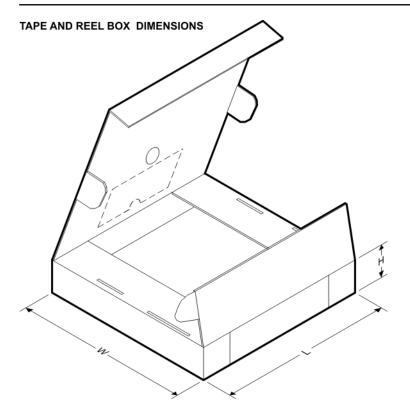
| *A | *All dimensions are nominal | | | | | | | | | | | | |
|----|-----------------------------|-------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| | Device | | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
| | TPS61085DGKR | VSSOP | DGK | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| | TPS61085DGKT | VSSOP | DGK | 8 | 250 | 180.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| | TPS61085PWR | TSSOP | PW | 8 | 2000 | 330.0 | 12.4 | 7.0 | 3.6 | 1.6 | 8.0 | 12.0 | Q1 |

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

3-Aug-2017



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TPS61085DGKR | VSSOP | DGK | 8 | 2500 | 367.0 | 367.0 | 35.0 |
| TPS61085DGKT | VSSOP | DGK | 8 | 250 | 210.0 | 185.0 | 35.0 |
| TPS61085PWR | TSSOP | PW | 8 | 2000 | 367.0 | 367.0 | 35.0 |

DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

- D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



DGK (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW0008A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



PW0008A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0008A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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